

## FYS4310. Problem 300-2. Suggested solution

Problem: construct semilog plot using table 3.2 and 3 contributions to diffusivity of phosphorous as a function of temperature from 700 ..1100 C

assume C of phosphorous is  $1e19 \text{ cm}^{-3}$

> **restart;**

Symbol definitions

$D_o$  = Diffusivity of P by neutral vacancy in intrinsic Si at infinite temperature in  $\text{cm}^2/\text{s}$

$E_a$  = activation energy for above in eV

$D_{om}$  = (  $D$  zero minus ) Diffusivity of P by negative vacancy in i-Si at inf. temperature

$E_{am}$  = activation energy for above

$D_{odm}$  = (  $D$  zero double minus ) Diffusivity of P by double negative vacancy diff in i-Si at inf. temperature

$E_{adm}$  = activation energy for above

Bolzmans constant

$T$  absolute temp i K

$n$  = electron concentration in  $\text{cm}^{-3}$

$n_i$  = intrinsic carrier concentration

$n_{io}$  = constant giving the intrinsic concentration

$E_g$  = Bangap of Si in eV

$E_{go}$  = Bangap at  $T=0$

$\alpha$ ,  $\beta$  = constants

$\Delta E_g$  = decrease in  $E_g$  at high doping

$N_D$  = Donor concentration

> **#assume (T>0, n>0, ni>0, ND>0, Ea>0, Eadm>0, Eam>0, Do>0, Dom>0, Dodm>0, k>0, nio>0, alpha>0, beta>0);**

The Diffusivity of P in Si can be written as

$$\begin{aligned} > eq1 := D = D_o e^{-\frac{E_a}{kT}} + \frac{D_{om} e^{-\frac{E_{am}}{kT}} n}{n_i} + D_{odm} e^{-\frac{E_{adm}}{kT}} \left( \frac{n}{n_i} \right)^2 \\ eq1 := D = D_o e^{-\frac{E_a}{kT}} + \frac{D_{om} e^{-\frac{E_{am}}{kT}} n}{n_i} + \frac{D_{odm} e^{-\frac{E_{adm}}{kT}} n^2}{n_i^2} \end{aligned}$$

The intrinsic carrier concentration is given by (see 3.8 in textbook )

$$\begin{aligned} > eq2 := n_i = n_{io} T^{\frac{3}{2}} e^{-\frac{E_g}{2kT}} \\ eq2 := n_i = n_{io} T^{3/2} e^{-\frac{1}{2} \frac{E_g}{kT}} \end{aligned}$$

The bandgap is given by (expt for highdoping effects) is given by (text book 3.9)

$$> eq3 := E_g = E_{go} - \frac{\alpha T^2}{\beta + T}$$

$$eq3 := E_g = E_{g0} - \frac{\alpha T^2}{\beta + T}$$

We discussed in the class whether to additionally include the bandgap narrowing due to high concentration. Some of that discussion can be found in another worksheet.

We decided to not include heavy doping effects on the bandgap because

- a) tgf did not believe the formulae we have available yield numerically reliable results.
- b) tgf thinks the underlying theoretical foundation is lacking and possibly quoted incorrect
- c) other corrections should also be applied for example the Fermi integral would theoretically describe the electron concentration than the Boltzmann approximation
- d) The high doping bandgap narrowing was not used when the diffusivities given in the table of the book was extracted from experimental data (again from concentration profiles)

So we do not here use equation (.3.10) and learned that 'life is not simple'

We have given the Phosphorous concentration,  $N_D$ , we need to find the electron concentration,  $n$ .

If we have no segregation or complex formation between point defects the relationship between them is given by charge neutrality yielding

$$> eq4 := n = N_D + \frac{n_i^2}{n}$$

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Which came from requirement of charge neutrality:  $N_D^+ - N_A^- + p - n = 0$  and assume complete ionization of donors by setting  $N_D^+ = N_D$ .

We solve eq4 for  $n$

**> eq5:=solve(eq4,n);**

$$eq5 := \frac{1}{2} N_D + \frac{1}{2} \sqrt{N_D^2 + 4 n_i^2}, \frac{1}{2} N_D - \frac{1}{2} \sqrt{N_D^2 + 4 n_i^2}$$

We definitely have to pick the solution with positive sign

**> if (is(op(0,eq5[1])='+')) then eq7:=n=eq5[1] else eq7:=n=eq5[2];  
fi;**

$$eq7 := n = \frac{1}{2} N_D + \frac{1}{2} \sqrt{N_D^2 + 4 n_i^2}$$

The numerical values of parameters in the previous equations are (as read from table 3.2, and on page 42-43) in units based on cm, eV, s and K

**> constants:={k=8.617065e-5, alpha=0.000473,Ego=1.17,beta=636,nio=7.3e15, Do=3.9,Ea=3.66,Dom=4.4,Eam=4,Dodm=44,Eadm=4.37,ND=1e19};**

*constants := {Dodm = 44, Dom = 4.4, Do = 3.9, Eadm = 4.37, Eam = 4, Ea = 3.66, Ego = 1.17, ND = 1.10<sup>19</sup>, α = 0.000473, β = 636, k = 0.00008617065, nio = 7.3 10<sup>15</sup>}*

Let us just estimate if we need to use equation eq7 or can use  $n=N_D$ .

We calculate  $n_i$  at 1000K and 1400K at low doping

We thus use the following equation

```
> eq8:=subs(eq3,eq2);
```

$$eq8 := ni = nio T^{3/2} e^{-\frac{1}{2} \frac{Ego - \frac{\alpha T^2}{\beta + T}}{k T}}$$

We calculate at a)T=1000K, b)T=1400K c)T=1273K (=1000 C)

We just put in the values of the symbols, calc at T=1000 and 1400 , and 1000C=1273 respectively

```
> eq9a:=evalf(subs(constants union {T=1000,ND=1e19},eq8));
eq9b:=evalf(subs(constants union {T=1400,ND=1e19},eq8));
eq9c:=evalf(subs(constants union {T=1273,ND=1e19},eq8));
```

$$eq9a := ni = 1.391660694 \cdot 10^{18}$$

$$eq9b := ni = 1.977654144 \cdot 10^{19}$$

$$eq9c := ni = 9.984573047 \cdot 10^{18}$$

So we can calculate n

```
> eq10a:=subs(constants union {eq9a},eq7);
eq10b:=subs(constants union {eq9b},eq7);
eq10c:=subs(constants union {eq9c},eq7);
```

$$eq10a := n = 1.019005968 \cdot 10^{19}$$

$$eq10b := n = 2.539881348 \cdot 10^{19}$$

$$eq10c := n = 1.616654373 \cdot 10^{19}$$

We have presented the equations we use, from this we can make the diffusivity an explicit function of temperature

We put eq8 into eq7 to get n and put n and ni (from eq8) into eq1 ,

The line below is doing exactly that

```
> Doft:=T->subs(constants,subs(subs(eq8,eq7),subs(eq8,eq1))):
```

We may also make each of the diffusion terms in eq1 an explicit function of temperature

In the following lines first for neutral vacancy contribution, negative vacancy and double negative vacancy.

```
> Do_ofT:=T->subs(constants,subs(subs(eq8,eq7),subs(eq8,Do*exp(-
Ea/k/T))))):
```

```
> Dm_ofT:=T->subs(constants,subs(subs(eq8,eq7),subs(eq8,Dom*exp(-
Eam/k/T)*n/ni))))):
```

```
> Ddm_ofT:=T->subs(constants,subs(subs(eq8,eq7),subs(eq8,Dodm*exp(-
Eadm/k/T)*(n/ni)^2))))):
```

We will calculate the diffusivity for a range of temperatures and plot

We decide to plot log(D) versus 1/T, thus we will pick values of (1/T) that are evenly spaced

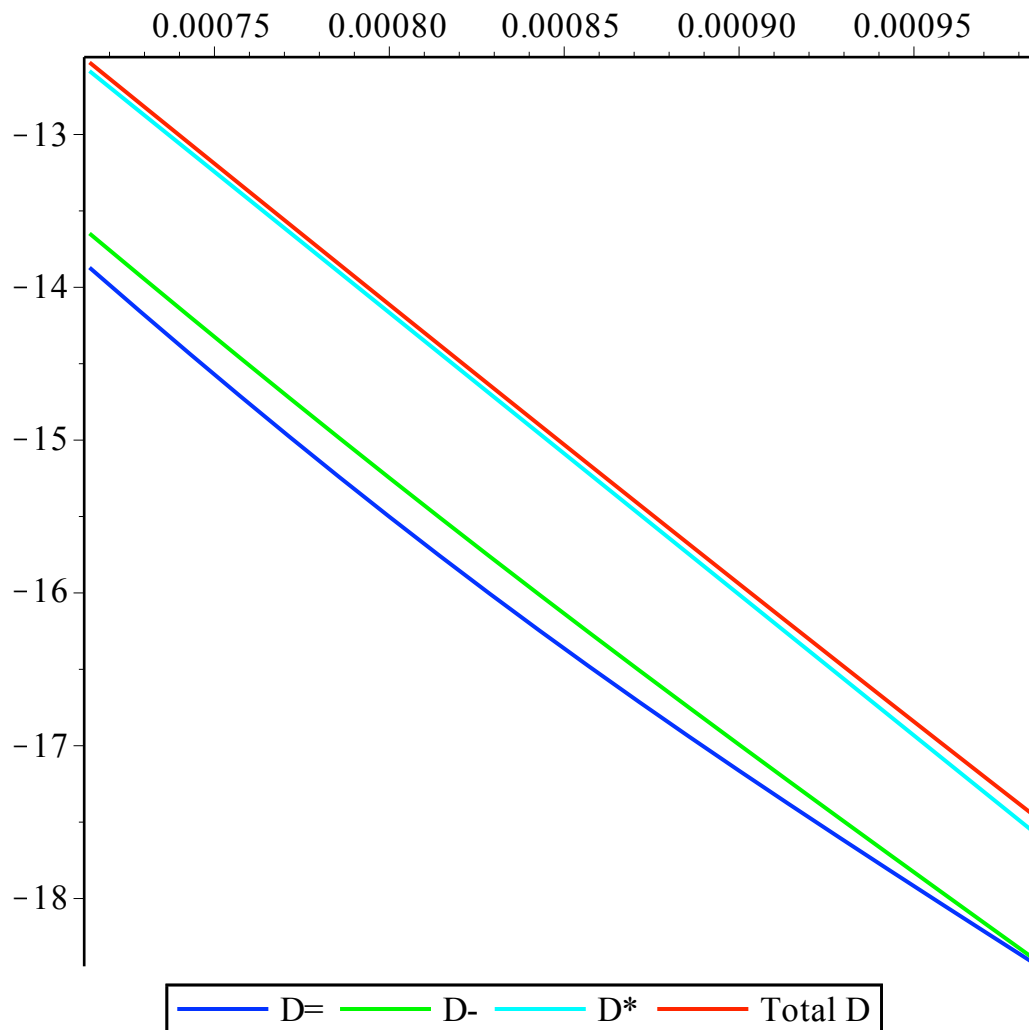
We will do this in a procedure

```

> with(plots):
> Makeplots:=proc()
  local j, invT, delinvT, TK, D , LogDarray,
    vD,vDo,vDm,vDdm,LogDoarray,LogDmarray,LogDdmarray,invTarray,
    dplot,doplot,dmplot,ddmplot:
  invT:=1.0/1400:## invT=1/T, we start at the highest temperature
  delinvT:=evalf((1/1000 -1/1400)/20.0):# we calculate the step size
  in 1/T
  for j from 1 to 20 do
    TK:=1/invT:
    vDo:=Do_ofT(TK);
    vDm:=evalf(eval(Dm_ofT(T),T=TK)):
    vDdm:=evalf(eval(Ddm_ofT(T),T=TK)):
    vD:=vDo+vDm+vDdm:
    LogDarray[j]:=evalf(log10(vD)):
    LogDoarray[j]:=evalf(log10(vDo)):
    LogDmarray[j]:=evalf(log10(vDm)):
    LogDdmarray[j]:=evalf(log10(vDdm)):
    invTarray[j]:=invT:
    invT:=invT+delinvT:
  od:
  dplot:=listplot([seq([invTarray[i],LogDarray[i]],i=1..20)],color=
  red):
  doplot:=listplot([seq([invTarray[i],LogDoarray[i]],i=1..20)],color=
  cyan):
  dmplot:=listplot([seq([invTarray[i],LogDmarray[i]],i=1..20)],color=
  green):
  ddmplot:=listplot([seq([invTarray[i],LogDdmarray[i]],i=1..20)],
  color=blue):
  display({dplot,doplot,dmplot,ddmplot});
end:

> Makeplots();

```



The above plot shows as  
 red = Total diffusivity  
 Cyan = the contribution from neutral vacancies  
 Green = the contribution from negative vacancies  
 Blue = the contribution from double negative vacancies  
 Axes horizontal  $1/T$  in  $(K^{-1})$  vertical  $\log_{10}$  to  $D$

We should compare the above figure with Data given in other books,  
 But textbooks only gives  $D_0$  and  $E_a$  values and figures and we dont know what they use for  $n$  and  $n_i$  to  
 extract the parameters.

[> **The End**